

902 483

**LAW OFFICES OF  
McGINN & GIBB, PLLC**

A PROFESSIONAL LIMITED LIABILITY COMPANY  
PATENTS, TRADEMARKS, COPYRIGHTS, AND INTELLECTUAL PROPERTY LAW  
8321 OLD COURTHOUSE ROAD, SUITE 200  
VIENNA, VIRGINIA 22182-3817  
TELEPHONE: (703) 761-4100  
FACSIMILE/DATA: (703) 761-2375; 761-2376  
E-MAIL: MCGINNGIBB@AOL.COM

SEAN M. MCGINN  
PHILLIP E. MILLER†  
FREDERICK E. COOPERRIDER†  
PETER A. BALNAVE, PH.D.  
FREDRIC J. ZIMMERMANT  
JAMES E. HOWARD†  
KENDAL M. SHEETS

CHRISTOPHER M. MCGINN\*

\*MEMBER OF BAR OTHER THAN VA  
\*PATENT ENGINEER (NON-ATTORNEY)

ANNAPOLIS, MD OFFICE  
FREDERICK W. GIBB, III  
LAWRENCE A. SCOTT†

June 13, 2003

**VIA FACSIMILE**

To: Examiner Erik J. Kielin  
Group Art Unit No. 2813  
U.S.P.T.O.

Facsimile No.: (703) 872-9318

**FAX RECEIVED**

From: Sean M. McGinn

Facsimile No.: (703) 761-2375 JUN 13 2003

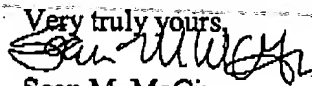
Re: Enclosed § 1.111 Amendment  
U.S. Patent Application Serial No. 09/902,483  
Our Ref: YOR.129CIP

TECHNOLOGY CENTER 2800

Dear Examiner Kielin:

Enclosed is an Amendment, responsive to the March 13, 2003 Office Action, which should place the above-referenced case in condition for allowance.

Thank you in advance for your kind consideration on this case.

Very truly yours,  
  
Sean M. McGinn

SMM/sm  
Enclosure

Total No. of Pages Transmitted: 17

09/902,483  
YOR919990408CIP

1

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Cabral et al.

Serial No.: 09/902,483

Group Art Unit: 2813

Filed: July 11, 2001

Examiner: Erik Kielin

For: SELF-ALIGNED SILICIDE (SALICIDE) PROCESS FOR LOW RESISTIVITY  
CONTACTS TO THIN FILM SILICON-ON-INSULATOR AND BULK MOSFETS  
AND FOR SHALLOW JUNCTIONS

Honorable Commissioner of Patents  
Alexandria, VA 22313-1450

AMENDMENT UNDER 37 C.F.R. §1.111

Sir:

FAX RECEIVED

In response to the Office Action dated March 13, 2003, please amend the above-  
identified application as follows:

JUN 13 2003

TECHNOLOGY CENTER 2800

IN THE CLAIMS:

5. (Amended) The method of claim 4, wherein said depositing of said metal containing silicon  
comprises performing a blanket deposition, wherein said metal comprises one of Co and Ti.

7. (Amended) The method of claim 6, wherein said blanket deposition is followed by a TiN cap  
deposition for preventing oxidation during a subsequent anneal processing.

8. (Amended) The method of claim 4, wherein said reacting of said metal containing silicon or  
said alloy comprises performing a first rapid thermal anneal (RTA) to form a metal-silicon phase,  
such that the deposited metal containing silicon with the underlying bulk silicon substrate,